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#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
	4Ω @ V <sub>GS</sub> = 10V	0.55A
300V	4Ω @ V <sub>GS</sub> = 4.5V	0.55A
	6Ω @ V <sub>GS</sub> = 2.7V	0.44A

### **Description**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

#### **Features**

- 0.6mm profile ideal for low profile applications
- PCB footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

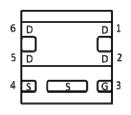
#### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (approximate)

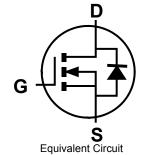




**Bottom View** 



Pin Out Bottom View



### Ordering Information (Note 4)

Part Number	Compliance	Case	Quantity per reel
DMN30H4D0LFDE-7	Standard	U-DFN2020-6	3,000
DMN30H4D0LFDE-13	Standard	U-DFN2020-6	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information



2H = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	201	3	2014		2015	20	16	2017		2018	2	2019
Code	Α		В		С		)	Е		F		G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	300	V
Gate-Source Voltage	$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	0.55 0.43	А
Pulsed Drain Current (10µs pulse, duty cycle ≦1%)	I <sub>DM</sub>	2	Α
Maximum Body Diode Continuous Current (Note 6)	I <sub>S</sub>	2	Α

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	Б	0.63	W	
Total Fower Dissipation	(Note 6)	P <sub>D</sub>	1.98	VV	
Thermal Desistance, Junction to Ambient	(Note 5)	-	189		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	61	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	9.3		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

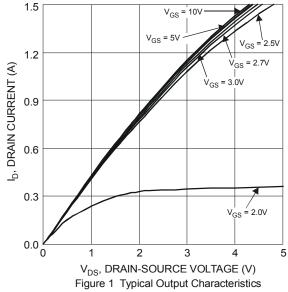
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

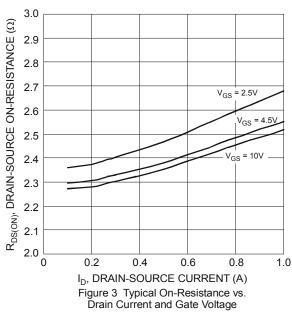
				1			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			5				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	300	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 240V, V <sub>GS</sub> = 0V	
Gate-Body Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	1.7	2.8	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	2.3	4		V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.3A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	2.3	4	Ω	$V_{GS} = 4.5V, I_D = 0.2A$	
		_	2.4	6		$V_{GS} = 2.7V, I_D = 0.1A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 0.3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	187.3	_			
Output Capacitance	Coss	_	11.7	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	8.7	_		1 - 1101112	
Total Gate Charge	Qg	_	7.6	_		V <sub>DS</sub> = 192V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5A	
Gate-Source Charge	Q <sub>gs</sub>	_	0.5	_	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	3.3	_		ID - 0.5A	
Turn-On Delay Time	t <sub>D(on)</sub>	_	4.9	_			
Turn-On Rise Time	t <sub>r</sub>	_	4.7	_		$V_{DS} = 60V, R_{L} = 200\Omega$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	25.8	_	nS	$V_{GS}$ = 10V, $R_G$ = 25 $\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	17.5	_			

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  Short duration pulse test used to minimize self-heating effect
  Guaranteed by design. Not subject to production testing







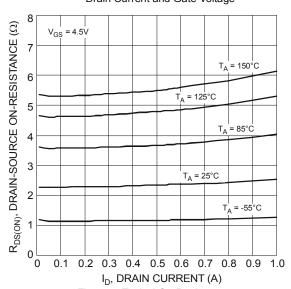


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

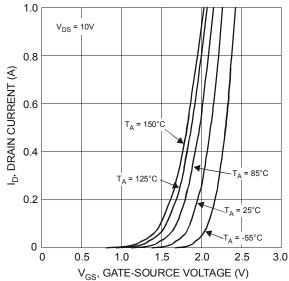


Figure 2 Typical Transfer Characteristics

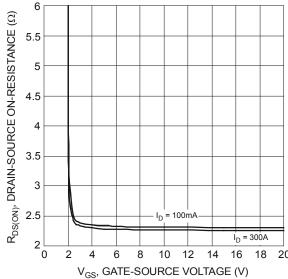


Figure 4 Typical Transfer Characteristics

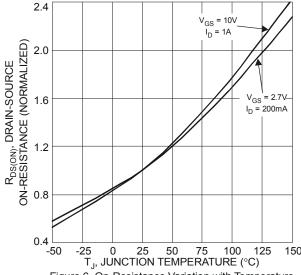
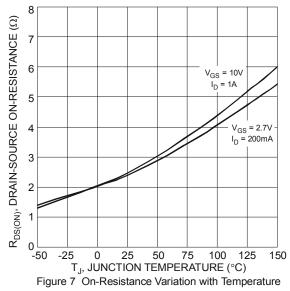
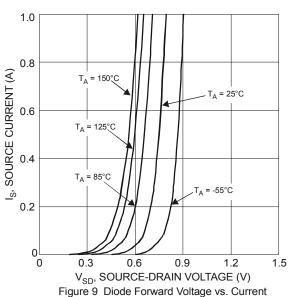
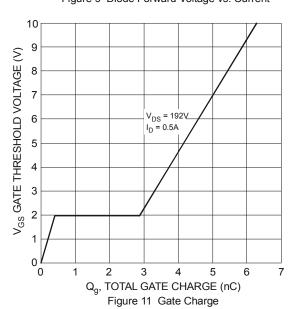


Figure 6 On-Resistance Variation with Temperature









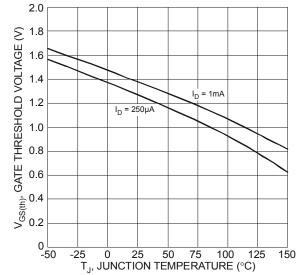
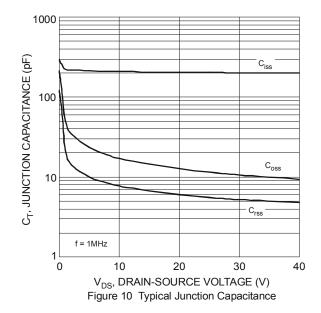
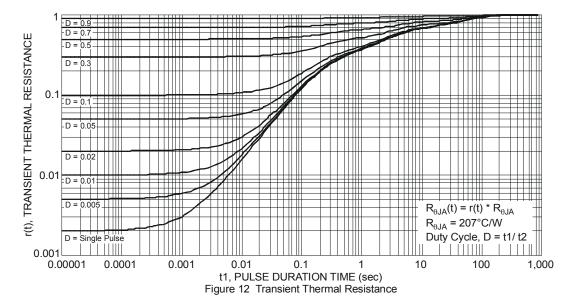


Figure 8 Gate Threshold Variation vs. Ambient Temperature

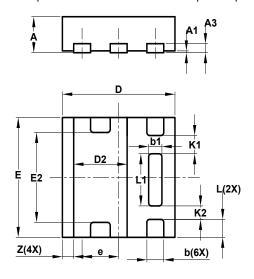






### **Package Outline Dimensions**

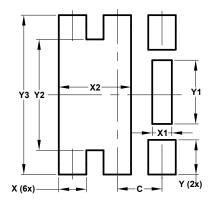
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6								
Type E								
Dim	Min Max Typ							
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3		_	0.15					
b	0.25	0.35	0.30					
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
Е	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
e		_	0.65					
L	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
K1			0.305					
K2	-	_	0.225					
Z			0.20					
All								

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value
Dillielisions	(in mm)
С	0.650
X	0.400
X1	0.285
X2	1.050
Υ	0.500
Y1	0.920
Y2	1.600
Y3	2.300



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